# N-Channel Enhancement Mode Power MOSFET

## Description

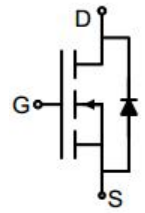
The GT025N06D5 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

## General Features

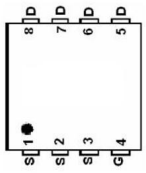
- $V_{DS}$ 60V
- $I_D$ (at $V_{GS}$ = 10V) 170A
- $R_{DS(ON)}$ (at $V_{GS}$ = 10V) < 2.3mΩ
- $R_{DS(ON)}$ (at $V_{GS}$ = 4.5V) < 3mΩ
- 100% Avalanche Tested
- RoHS Compliant

## Application

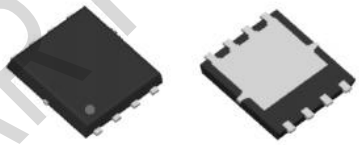
- Power switch
- DC/DC converters
- Synchronous Rectification




Schematic Diagram




pin assignment



DFN5X6-8L

PRELIMINARY

| Device | Package | Marking | Packaging |
|---|---|---|---|
| GT025N06D5 | DFN5X6-8L | GT025N06 | 5000pcs/Reel |

## Absolute Maximum Ratings $T_C$ = 25ºC, unless otherwise noted

| Parameter | | Symbol | Value | Unit |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | 60 | V |
| Continuous Drain Current | $T_C$ = 25ºC | $I_D$ | 170 | A |
| | $T_C$ = 100ºC | | 107 | |
| Pulsed Drain Current (note1) | | $I_{DM}$ | 680 | A |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | V |
| Power Dissipation | | $P_D$ | 215 | W |
| Single pulse avalanche energy （note2） | | $E_{AS}$ | 420 | mJ |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | -55 To 150 | ºC |

## Thermal Resistance

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Thermal Resistance, Junction-to-Ambient | $R_{thJA}$ | 50 | ºC/W |
| Thermal Resistance, Junction-to-Case | $R_{thJC}$ | 0.58 | ºC/W |

**Specifications** $T_J$ = 25ºC, unless otherwise noted

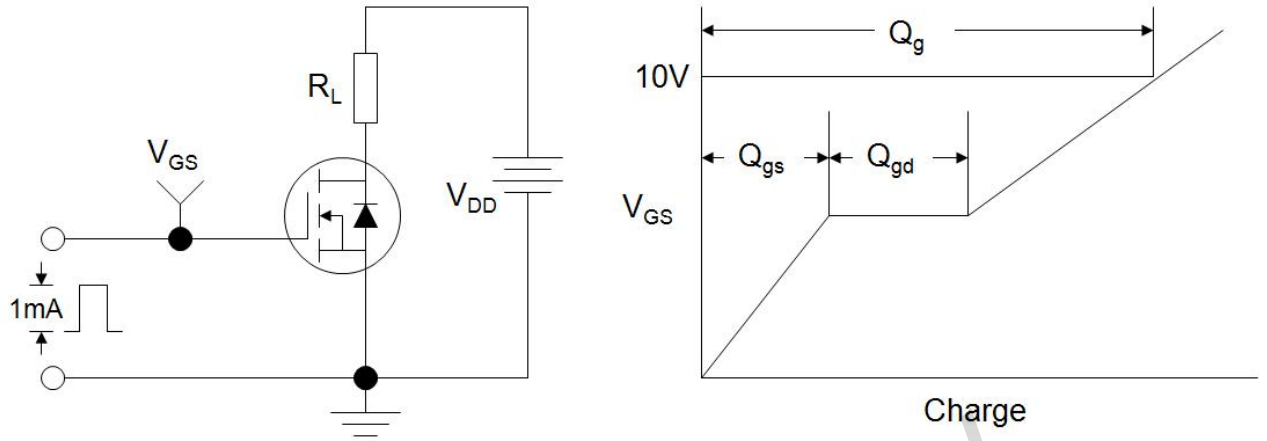
| Parameter | Symbol | Test Conditions | Value | | | Unit |
|---|---|---|---|---|---|---|
| | | | Min. | Typ. | Max. | |
| **Static Parameters** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0V, $I_D$ = 250μA | 60 | -- | -- | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 60V, $V_{GS}$ = 0V | -- | -- | 1 | μA |
| Gate-Source Leakage | $I_{GSS}$ | $V_{GS}$ = ±20V | -- | -- | ±100 | nA |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250μA | 1.2 | 1.9 | 2.5 | V |
| Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10V, $I_D$ = 50A | -- | 2.0 | 2.3 | mΩ |
| | | $V_{GS}$ = 4.5V, $I_D$ = 25A | -- | 2.6 | 3.0 | |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$ = 5V,$I_D$ = 50A | -- | 60 | -- | S |
| **Dynamic Parameters** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0V, $V_{DS}$ = 30V, f = 0.8MHz | -- | 5300 | -- | pF |
| Output Capacitance | $C_{oss}$ | | -- | 1400 | -- | |
| Reverse Transfer Capacitance | $C_{rss}$ | | -- | 70 | -- | |
| Total Gate Charge | $Q_g$ | $V_{DD}$ = 30V, $I_D$ = 50A, $V_{GS}$ = 10V | -- | 70 | -- | nC |
| Gate-Source Charge | $Q_{gs}$ | | -- | 21 | -- | |
| Gate-Drain Charge | $Q_{gd}$ | | -- | 16 | -- | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}$ = 30V, $I_D$ = 50A, $R_G$ = 3Ω | -- | 16 | -- | ns |
| Turn-on Rise Time | $t_r$ | | -- | 9 | -- | |
| Turn-off Delay Time | $t_{d(off)}$ | | -- | 36 | -- | |
| Turn-off Fall Time | $t_f$ | | -- | 11 | -- | |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous Body Diode Current | $I_S$ | $T_C$ = 25ºC | -- | -- | 170 | A |
| Body Diode Voltage | $V_{SD}$ | $T_J$ = 25ºC, $I_{SD}$ = 50A, $V_{GS}$ = 0V | -- | -- | 1.2 | V |
| Reverse Recovery Chrage | Qrr | $I_F$ = 50A, $V_{GS}$ = 0V di/dt=500A/us | | 150 | -- | nC |
| Reverse Recovery Time | Trr | | | 30 | -- | ns |

PRELIMINARY

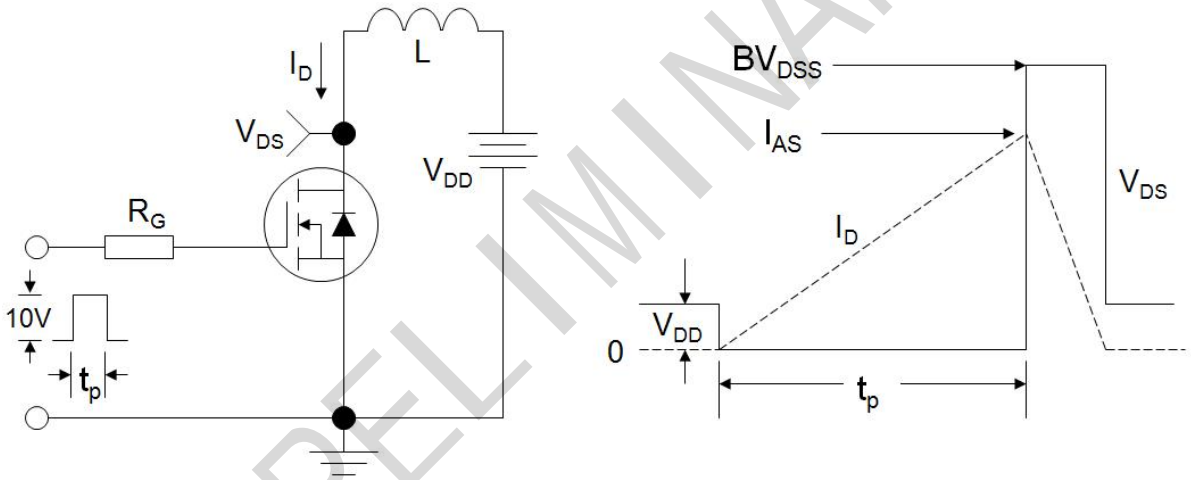
**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=50V,VGS=10V,L=0.5mH,Rg=25Ω
   The table shows the minimum avalanche energy, which is 1156mJ when the device is tested until failure
3. Identical low side and high side switch with identical $R_G$

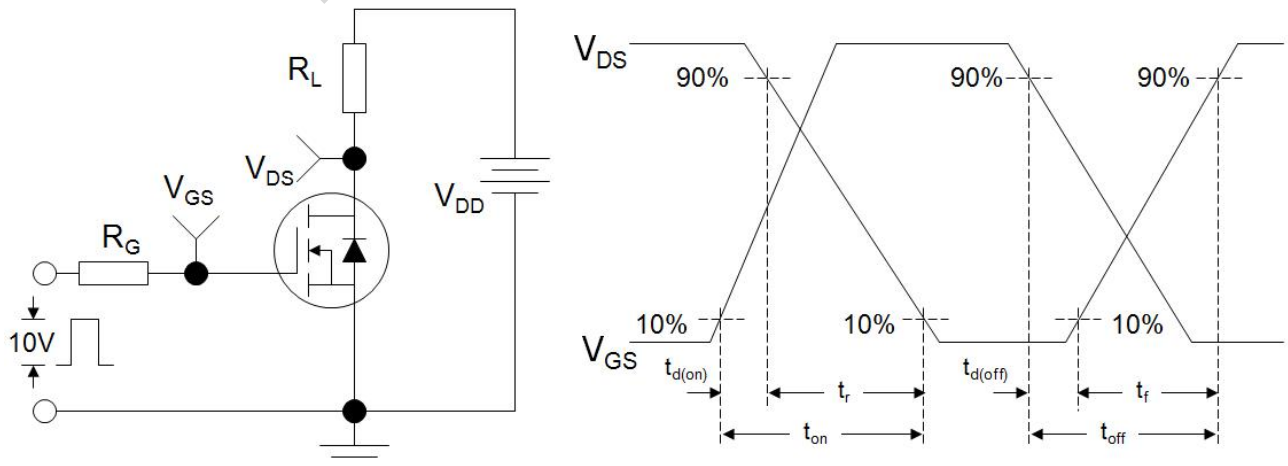
**Gate Charge Test Circuit**




**EAS Test Circuit**




**Switch Time Test Circuit**




PRELIMINARY

**Typical Characteristics** $T_J$ = 25ºC, unless otherwise noted

**Figure 1. Output Characteristics**

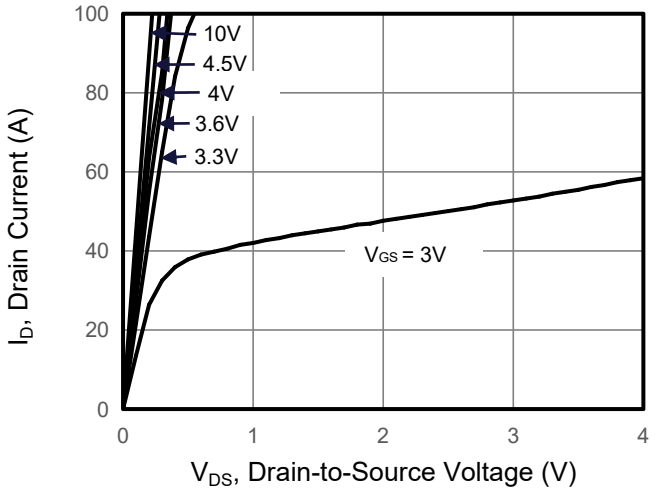



**Figure 2. Transfer Characteristics**

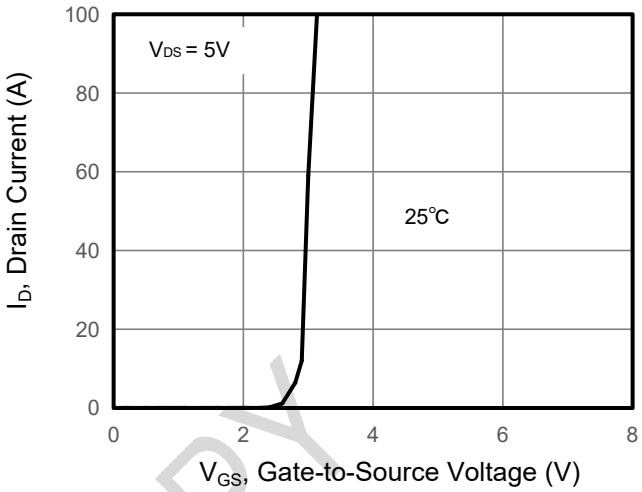



**Figure 3. Drain Source On Resistance**

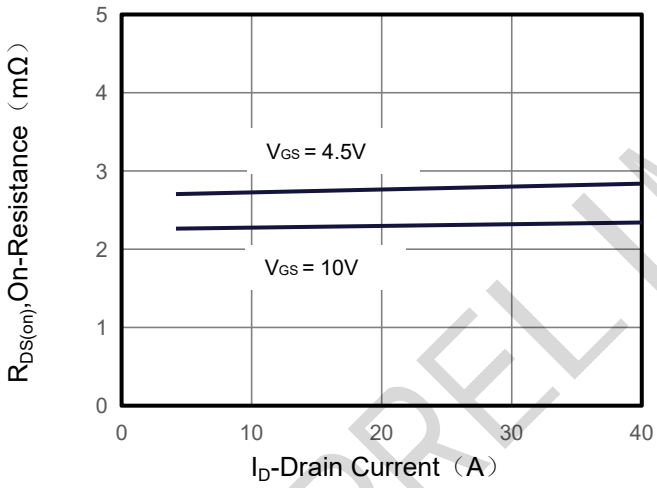



**Figure 4. Gate Charge**

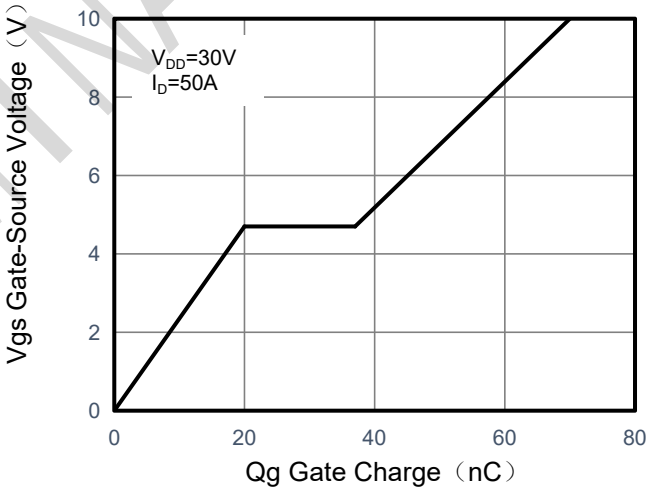



**Figure 5. Capacitance**

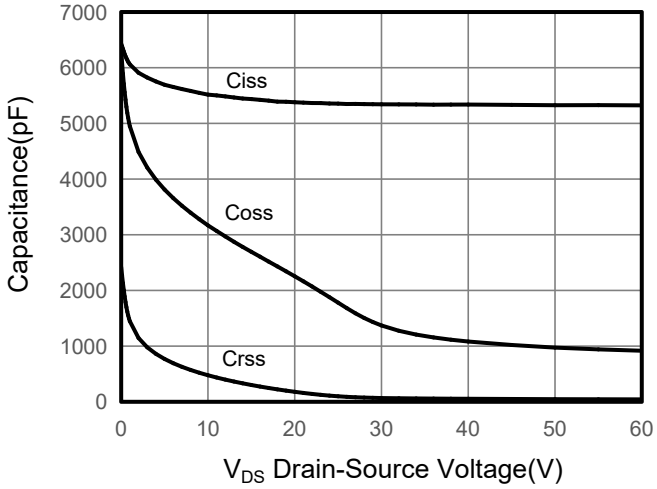
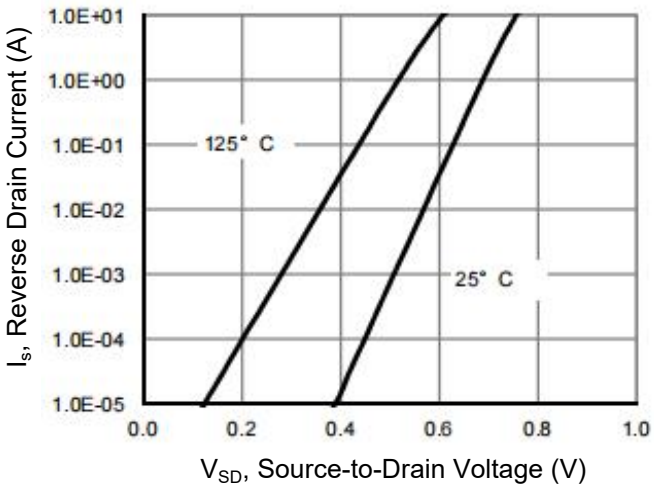



**Figure 6. Source-Drain Diode Forward**




PRELIMINARY

## Typical Characteristics $T_J$ = 25ºC, unless otherwise noted

**Figure 7. Drain-Source On-Resistance**

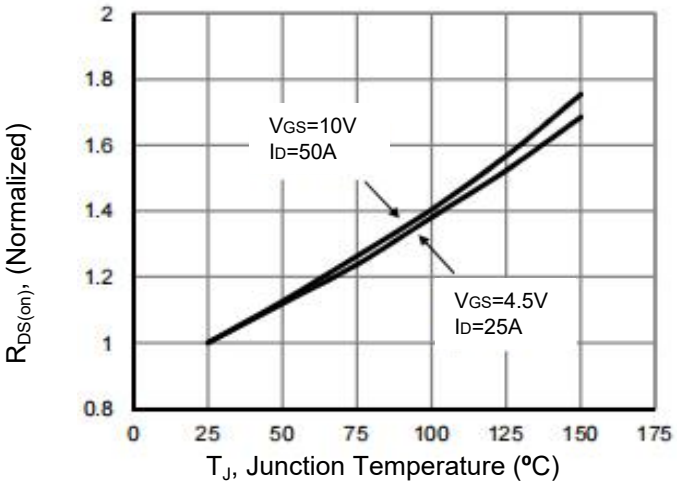



**Figure 8. Safe Operation Area**

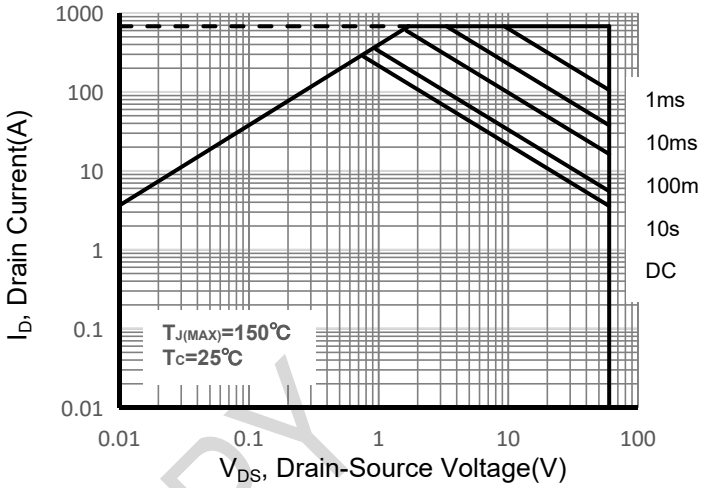
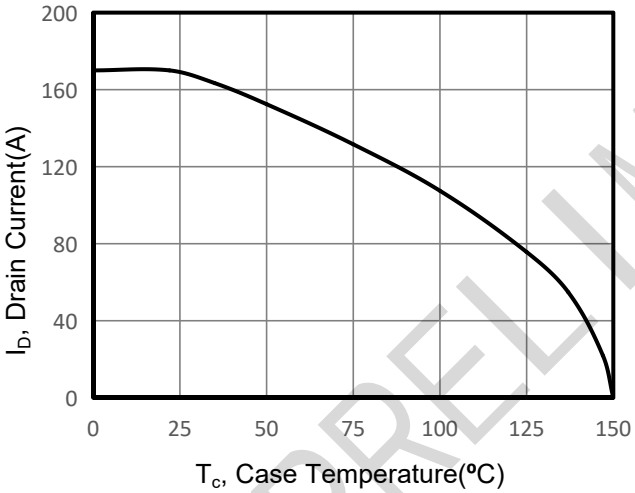
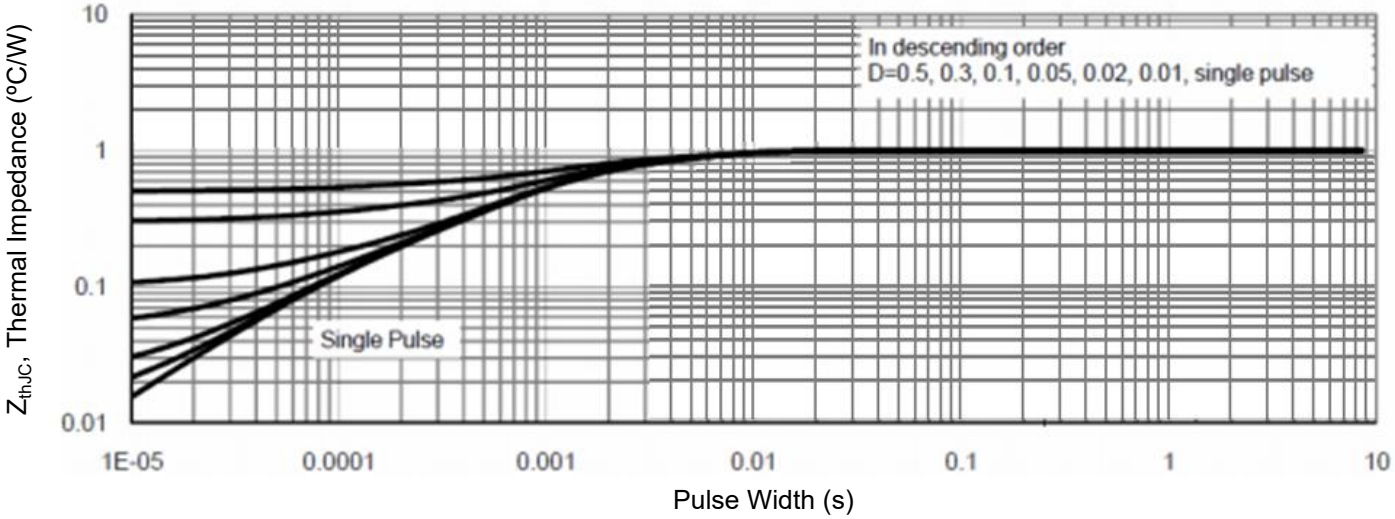



**Figure 9. Maximum Continuous Drain Current vs Case Temperature**

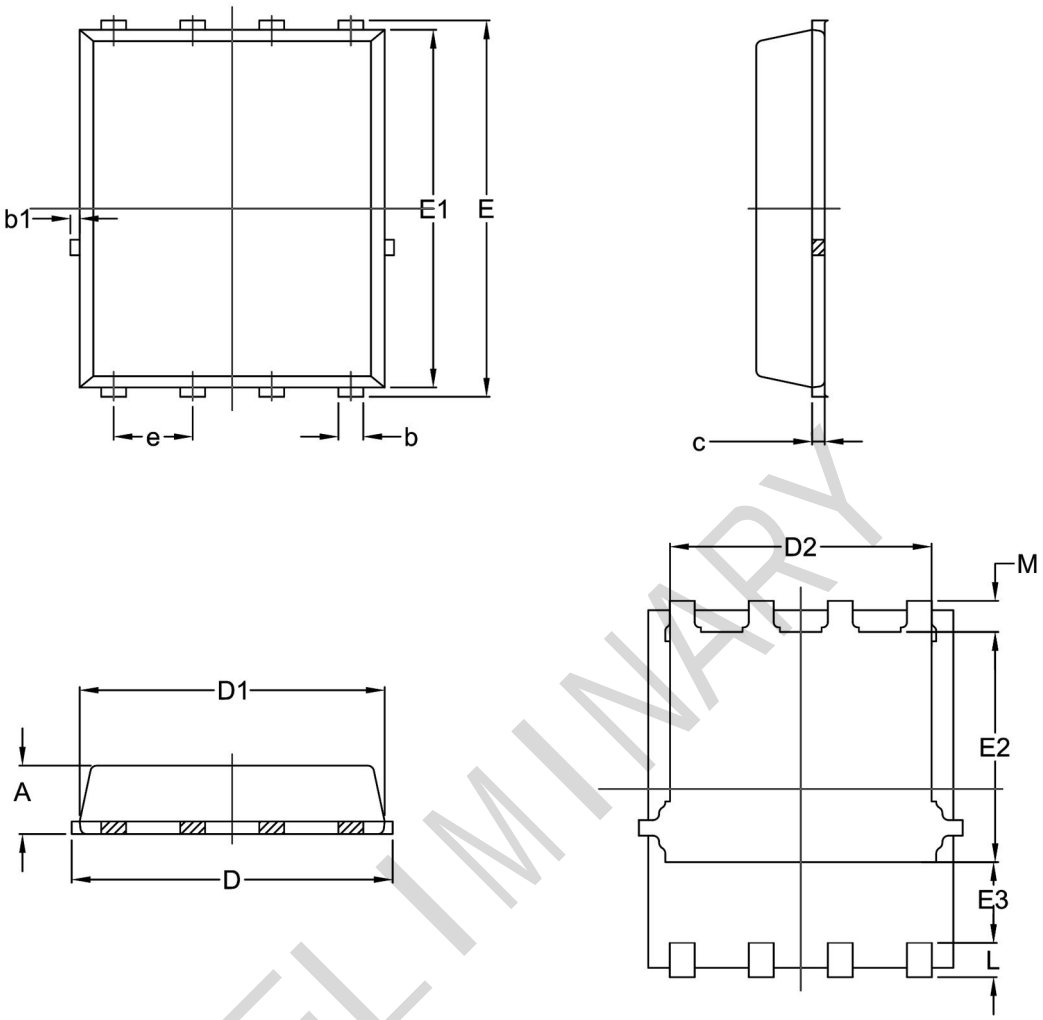



PRELIMINARY

**Figure 10. Normalized Maximum Transient Thermal Impedance**



**DFN5X6-8L Package Information**




PRELIMINARY

| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN | NOM | MAX |
| A | 1.00 | 1.10 | 1.20 |
| b | 0.30 | 0.40 | 0.50 |
| b1 | 0.02 | 0.15 | 0.22 |
| c | 0.15 | 0.20 | 0.35 |
| D | 4.95 | 5.15 | 5.35 |
| D1 | 4.80 | 4.90 | 5.00 |
| D2 | 4.00 | 4.20 | 4.40 |
| E | 5.95 | 6.05 | 6.25 |
| E1 | 5.65 | 5.75 | 5.85 |
| E2 | 3.50 | 3.70 | 3.90 |
| E3 | 1.10 | / | / |
| e | 1.27 | | |
| L | 0.40 | 0.55 | 0.70 |
| M | 0.35 | 0.50 | 0.65 |